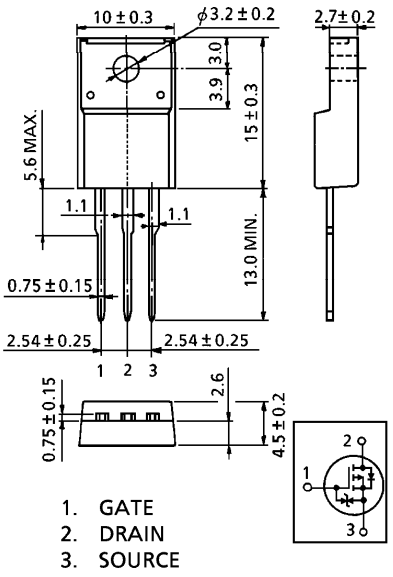
TOSHIBA FIELD EFFECT TRANSISTOR SILICON P CHANNEL MOS TYPE (L^2-π-MOSV)

2SJ380

RELAY DRIVE, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

- 4 V Gate Drive
- Low Drain-Source ON Resistance : $R_{DS\,(ON)} = 0.15\ \Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 7.7$ S (Typ.)
- Low Leakage Current : $I_{DSS} = -100\ \mu$A (Max.) ($V_{DS} = -100$ V)
- Enhancement-Mode : $V_{th} = -0.8 \sim -2.0$ V ($V_{DS} = -10$ V, $I_D = -1$ mA)

Unit in mm



JEDEC	—
JEITA	SC-67
TOSHIBA	2-10R1B

Weight : 1.9 g (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	−100	V
Drain-Gate Voltage ($R_{GS} = 20\ k\Omega$)		V_{DGR}	−100	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	DC (Note 1)	I_D	−12	A
	Pulse (Note 1)	I_{DP}	−48	A
Drain Power Dissipation (Tc = 25°C)		P_D	35	W
Single Pulse Avalanche Energy (Note 2)		E_{AS}	312	mJ
Avalanche Current		I_{AR}	−12	A
Repetitive Avalanche Energy (Note 3)		E_{AR}	3.5	mJ
Channel Temperature		T_{ch}	150	°C
Storage Temperature Range		T_{stg}	−55~150	°C

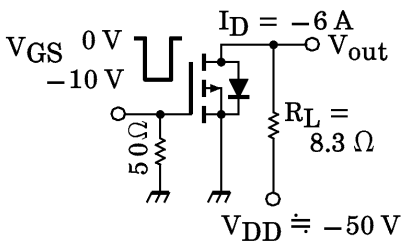
THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th\,(ch\text{-}c)}$	3.57	°C / W
Thermal Resistance, Channel to Ambient	$R_{th\,(ch\text{-}a)}$	62.5	°C / W

(Note 1) : Please use devices on condition that the channel temperature is below 150°C.
(Note 2) : $V_{DD} = -25$ V, $T_{ch} = 25$°C (initial), L = 2.94 mH, $R_G = 25\ \Omega$, $I_{AR} = -12$ A
(Note 3) : Repetitive rating ; Pulse Width Limited by maximum junction temperature.

This transistor is an electrostatic sensitive device.
Please handle with caution.

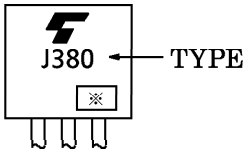
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 16$ V, $V_{DS} = 0$ V	—	—	±10	μA
Drain Cut-off Current		I_{DSS}	$V_{DS} = -100$ V, $V_{GS} = 0$ V	—	—	−100	μA
Drain-Source Breakdown Voltage		$V_{(BR)\,DSS}$	$I_D = -10$ mA, $V_{GS} = 0$ V	−100	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = -10$ V, $I_D = -1$ mA	−0.8	—	−2.0	V
Drain-Source ON Resistance		$R_{DS\,(ON)}$	$V_{GS} = -4$ V, $I_D = -6$ A	—	0.25	0.32	Ω
			$V_{GS} = -10$ V, $I_D = -6$ A	—	0.15	0.21	
Forward Transfer Admittance		$\|Y_{fs}\|$	$V_{DS} = -10$ V, $I_D = -6$ A	4.5	7.7	—	S
Input Capacitance		C_{iss}	$V_{DS} = -10$ V, $V_{GS} = 0$ V, f = 1 MHz	—	1100	—	pF
Reverse Transfer Capacitance		C_{rss}		—	200	—	
Output Capacitance		C_{oss}		—	440	—	
Switching Time	Rise Time	t_r		—	18	—	ns
	Turn-on Time	t_{on}		—	30	—	
	Fall Time	t_f		—	18	—	
	Turn-off Time	t_{off}	Duty ≦ 1%, $t_w = 10$ μs	—	65	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} \fallingdotseq -80$ V, $V_{GS} = -10$ V, $I_D = -12$ A	—	48	—	nC
Gate-Source Charge		Q_{gs}		—	29	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	19	—	

SOURCE-DRAIN RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current (Note 1)	I_{DR}	—	—	—	−12	A
Pulse Drain Reverse Current (Note 1)	I_{DRP}	—	—	—	−48	A
Forward Voltage (Diode)	V_{DSF}	$I_{DR} = -12$ A, $V_{GS} = 0$ V	—	—	1.7	V
Reverse Recovery Time	t_{rr}	$I_{DR} = -12$ A, $V_{GS} = 0$ V, $dI_{DR}/dt = 50$ A/μs	—	160	—	ns
Reverse Recovery Charge	Q_{rr}		—	0.5	—	μC

MARKING

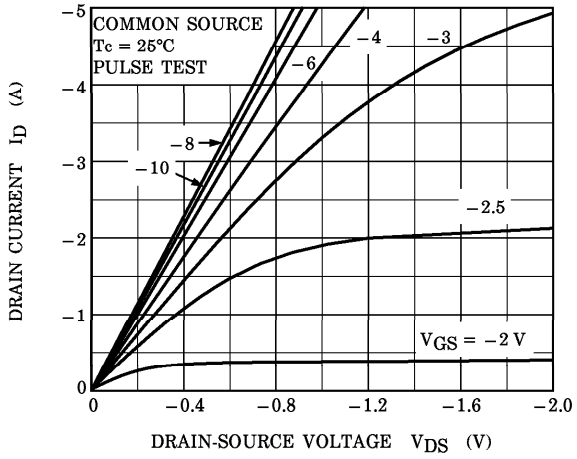


※ Lot Number

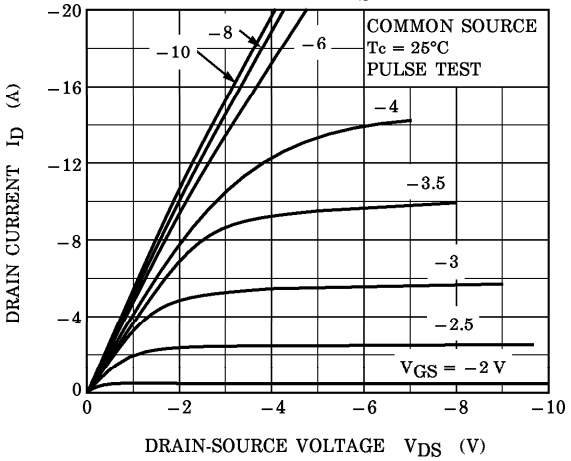
□□ — Month (Starting from Alphabet A)

Year (Last Number of the Christian Era)

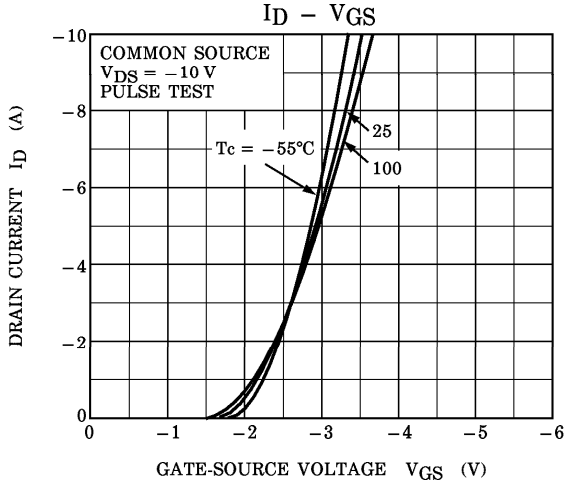
$I_D - V_{DS}$



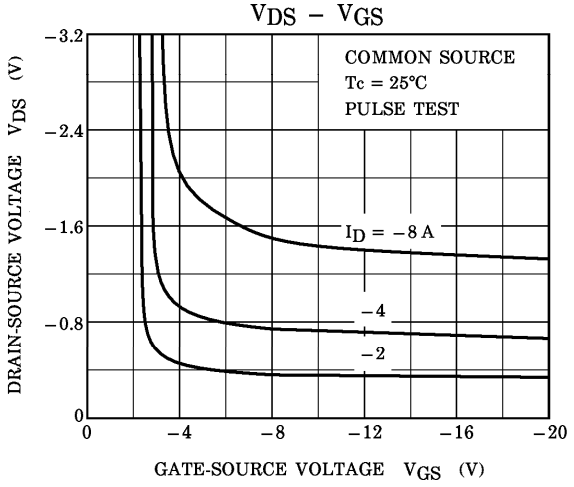
$I_D - V_{DS}$



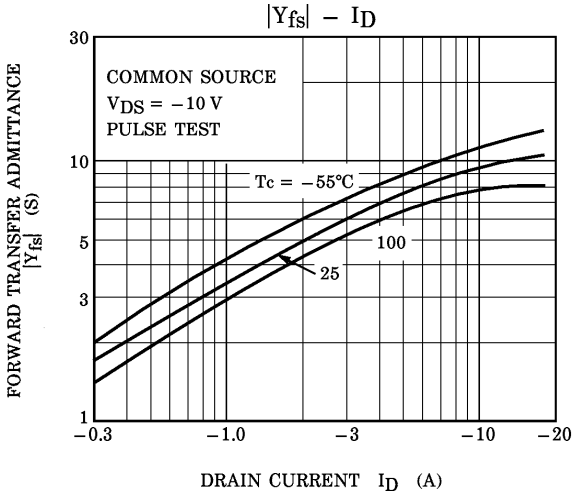
$I_D - V_{GS}$



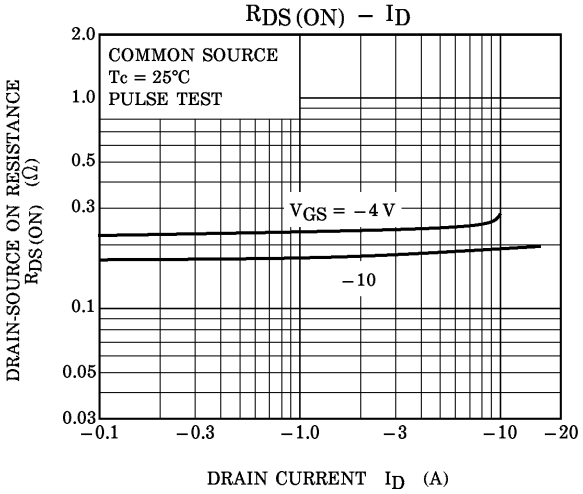
$V_{DS} - V_{GS}$



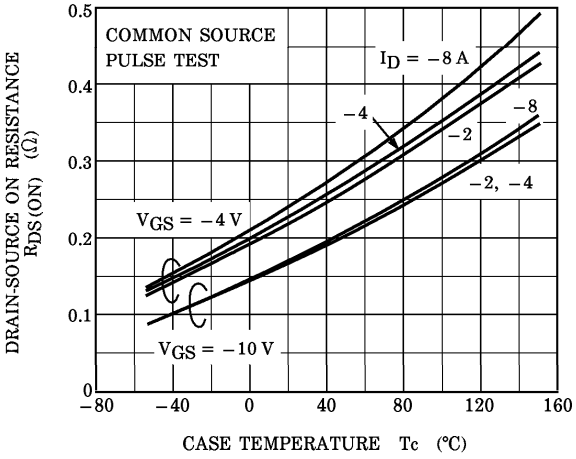
$|Y_{fs}| - I_D$



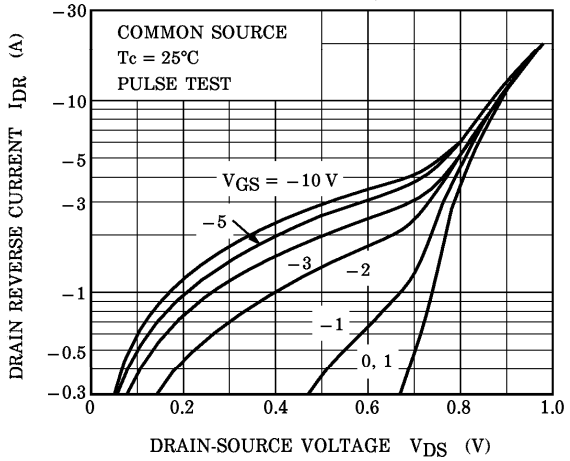
$R_{DS\,(ON)} - I_D$



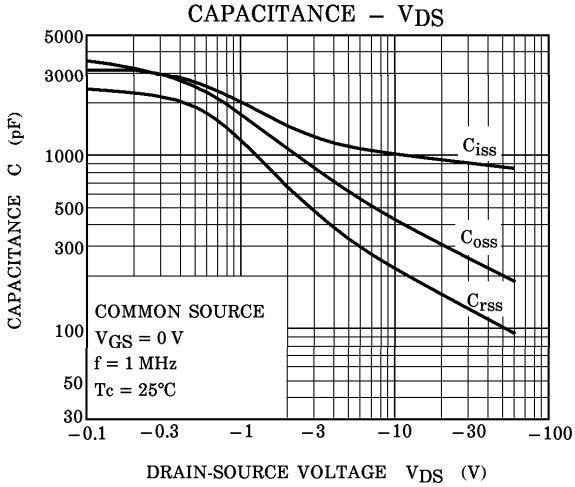
$R_{DS\,(ON)}$ – Tc



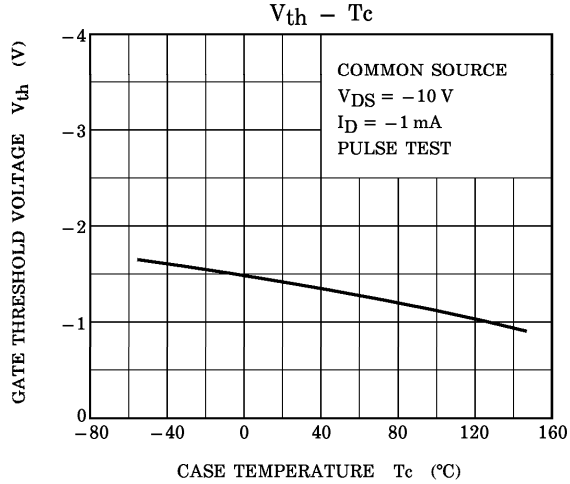
I_{DR} – V_{DS}



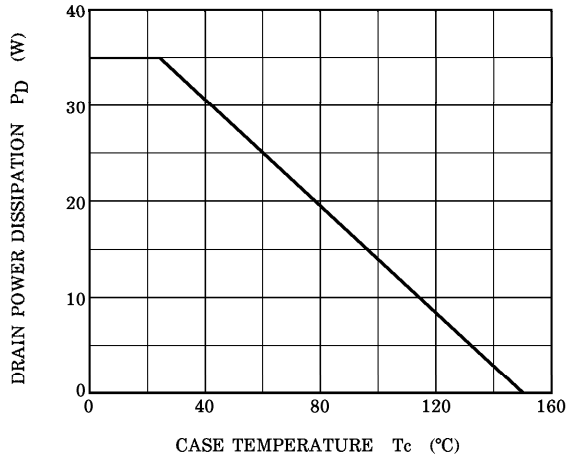
CAPACITANCE – V_{DS}



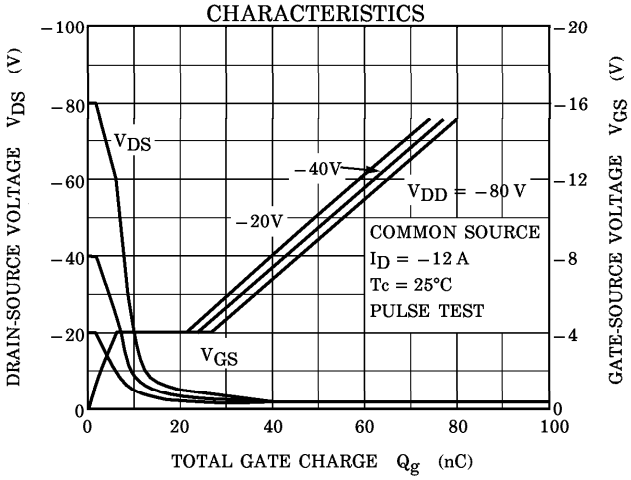
V_{th} – Tc



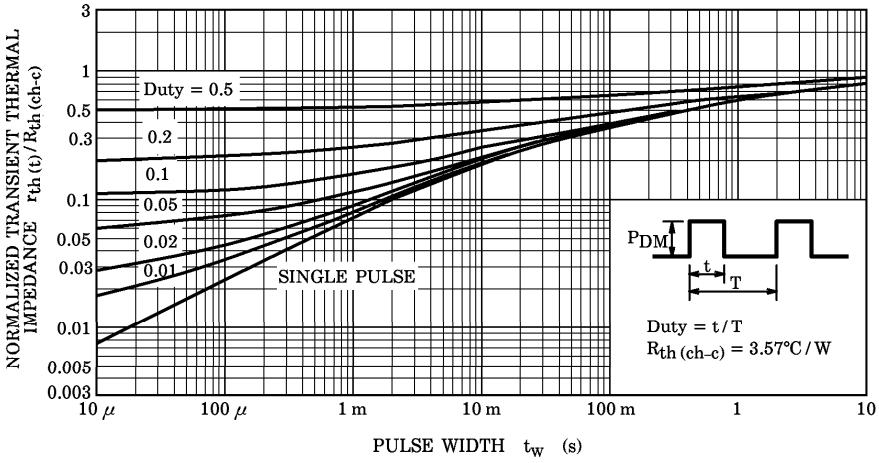
P_D – Tc



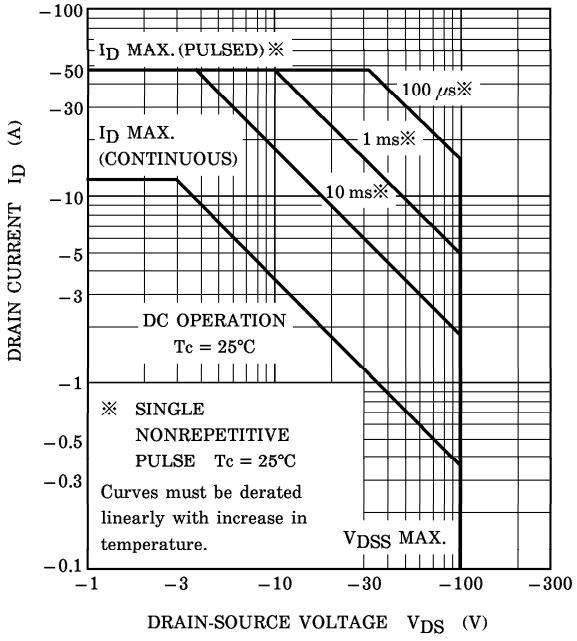
DYNAMIC INPUT / OUTPUT CHARACTERISTICS



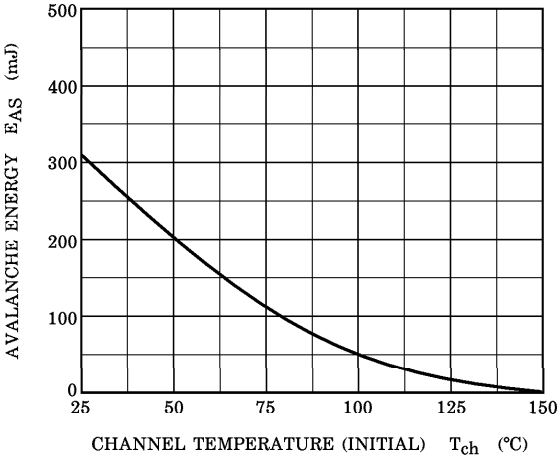
r_{th} – t_w

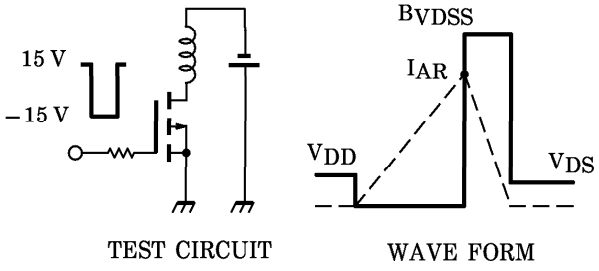


SAFE OPERATING AREA



E_{AS} – T_{ch}





$R_G = 25\ \Omega$
$V_{DD} = -25$ V, L = 2.94 mH

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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